

isc Silicon NPN Power Transistor

2SC2690

DESCRIPTION

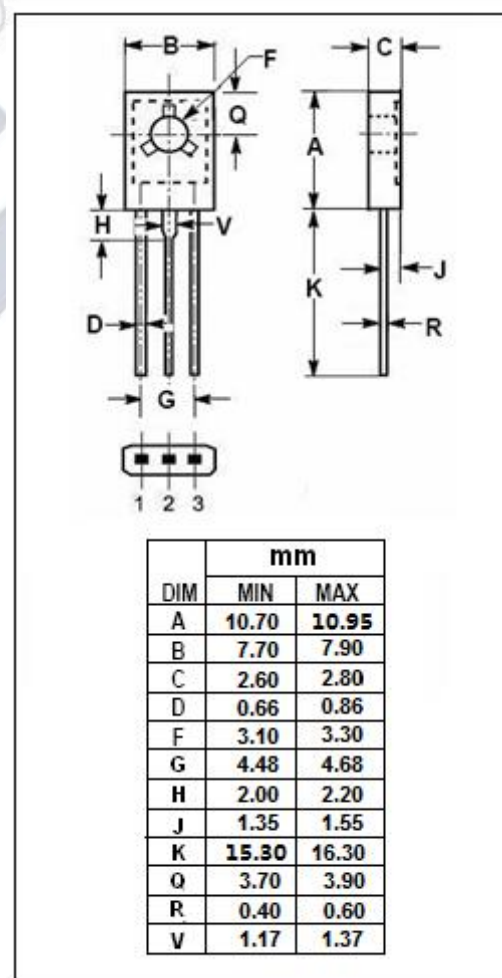
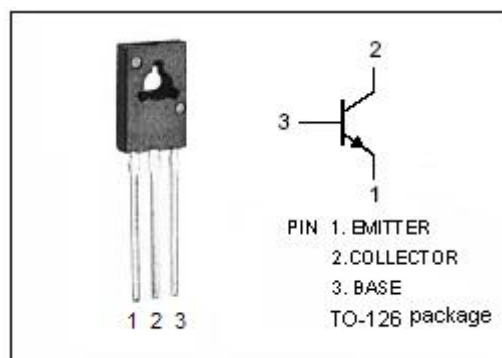
- High voltage and high f_T
- Complementary to 2SA1220 PNP transistor
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- The 2SC2690 is general purpose transistors designed For use in audio and radio frequency power amplifiers.
- Suitable for use in driver stage of 50 to 100W audio Amplifiers and output stage of TV vertical deflection circuit

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	120	V
V_{CER}	Collector-Emitter Voltage $R_{BE}=150\ \Omega$	120	V
V_{CEO}	Collector-Emitter Voltage	120	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	1.2	A
P_C	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	20	W
T_J	Junction Temperature	-55~150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon NPN Power Transistor**2SC2690****ELECTRICAL CHARACTERISTICS** $T_c=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=1\text{A}; I_B=200\text{mA}$			0.7	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=1\text{A}; I_B=200\text{mA}$			1.3	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=120\text{V}; I_E=0$			1	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			1	μA
h_{FE-1}	DC Current Gain	$I_C=5\text{mA}; V_{CE}=5\text{V}$	35			
h_{FE-2}	DC Current Gain	$I_C=0.3\text{A}; V_{CE}=5\text{V}$	60		320	

◆ **h_{FE-2} Classifications**

R	Q	P
60-120	100-200	160-320